

**Silicon NPN Power Transistors**

**2SC4762**

**DESCRIPTION**

- With TO-3P(H)IS package
- High voltage,high speed
- Low saturation voltage
- Bult-in damper diode

**APPLICATIONS**

## Silicon NPN Power Transistors

## 2SC4762

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =300mA ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =1500V ; I <sub>E</sub> =0			1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V ; I <sub>C</sub> =0	83		250	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8	12		
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	5		9	
C <sub>ob</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V, f=1MHz		170		pF
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =5A		1.25	1.8	V
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V	1	3		MHz

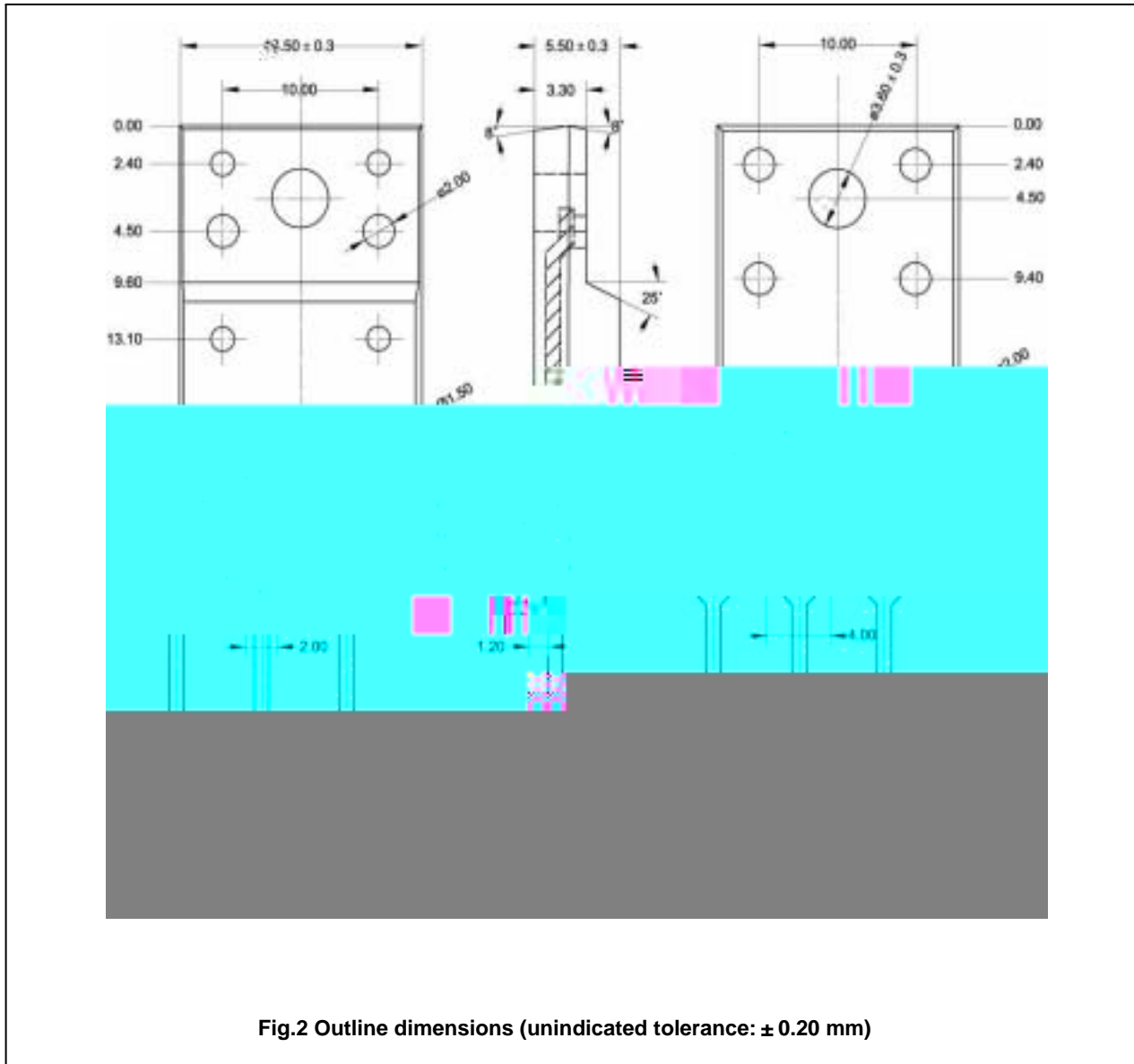
Switching times resistive load

t <sub>s</sub>	Storage time	I <sub>CP</sub> =5A ; I <sub>B1</sub> =1A I <sub>B2</sub> =-2A ; R <sub>L</sub> =39		1.8	3.0	μs
t <sub>f</sub>	Fall time			0.1	0.2	μs

S116F8 NPN Power Transistors

2SC4762

PACKAGE OUTLINE



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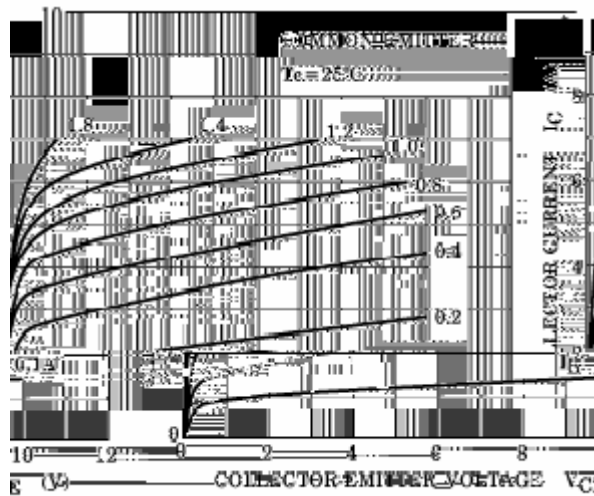


Fig.3 Static Characteristic

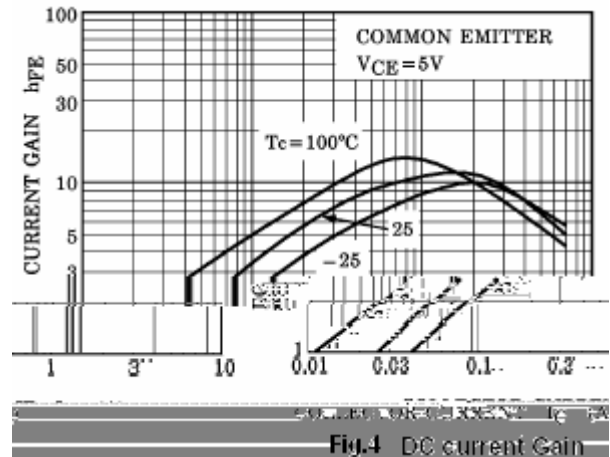


Fig.4 DC current Gain

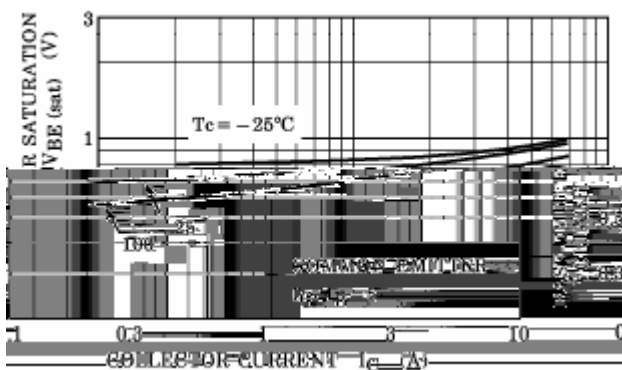


Fig.5 Base-Emitter Saturation Voltage

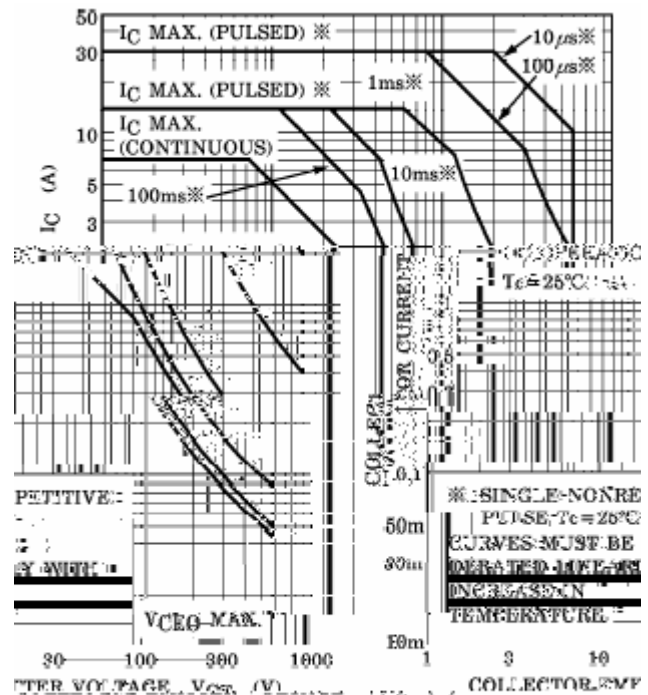


Fig.6 Safe Operating Area